

METHOD FOR CORRECTING MEASURED DATA OF ELECTRON BEAM MICRO-ANALYZER

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Abstract

PROBLEM TO BE SOLVED: To improve a measurement accuracy of an electron beam micro- analyzer when a sample is a thin film or a minute part.

SOLUTION: X-ray intensity data of a linear analysis or a mapping analysis is obtained by scanning linearly or two-dimensionally on the sample by the electron beam micro-analyzer and measuring X rays generated by the excitation of incident electron beams. Measured data are corrected by a step of estimating an X-ray generation region for every element included in the sample on the basis of an accelerating voltage of the incident electron beams, and a step of correcting the measured X-ray intensity data on the basis of a ratio of a measurement object part in the estimated X-ray generation region to find an intensity of X rays generated from the measurement object part.

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